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(71) Applicant: **APPLIED MATERIALS, INC.** [US/US]; 3050 Bowers Avenue, Santa Clara, California 95054 (US).

(72) Inventors: **SHENG, Shuran**; 3050 Bowers Avenue, Santa Clara, California 95054 (US). **ZHANG, Lin**; 3050 Bowers Avenue, Santa Clara, California 95054 (US). **WERNER, Joseph C.**; 3050 Bowers Avenue, Santa Clara, California 95054 (US).

(74) Agent: **MCCORMICK, Daniel K.** et al.; 1100 Peachtree Street NE, Suite 2800, Mailstop: IP Docketing - 22, Atlanta, Georgia 30309 (US).

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(54) Title: LID STACK FOR HIGH FREQUENCY PROCESSING

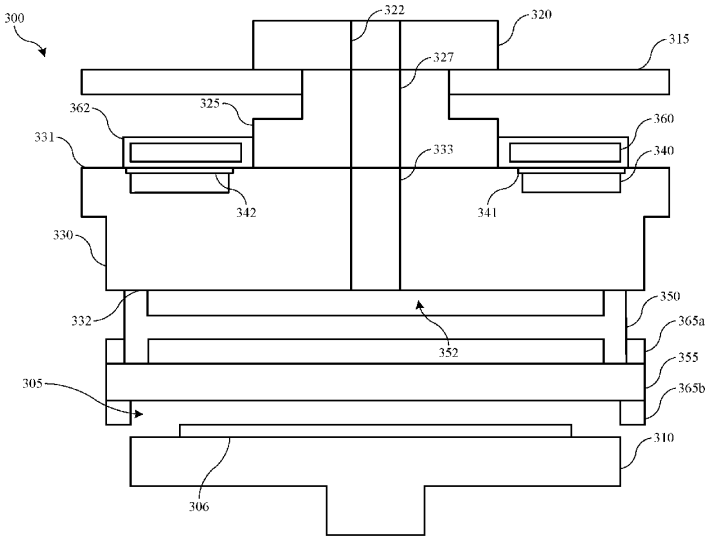

FIG. 3

(57) Abstract: Exemplary semiconductor processing chambers may include a substrate support positioned within a processing region of the semiconductor processing chamber. The chamber may include a lid plate. The chamber may include a gasbox positioned between the lid plate and the substrate support. The gasbox may be characterized by a first surface and a second surface opposite the first surface. The gasbox may define a central aperture. The gasbox may define an annular channel in the first surface of the gasbox extending about the central aperture through the gasbox. The gasbox may include an annular cover extending across the annular channel defined in the first surface of the gasbox. The chamber may include a blocker plate positioned between the gasbox and the substrate support. The chamber may include a ferrite block positioned between the lid plate and the blocker plate.

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